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List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Highly Linear High-Power 802.11ac/ax WLAN SiGe HBT Power Amplifiers With a Compact 2nd-Harmonic-Shorted Four-Way Transformer and a Thermally Compensating Dynamic Bias Circuit. IEEE Journal of Solid-State Circuits, 2020, 55, 2356-2370.	5.4	26
2	A Compact, Wideband Lumped-Element Wilkinson Power Divider/Combiner Using Symmetric Inductors with Embedded Capacitors. IEEE Microwave and Wireless Components Letters, 2016, 26, 595-597.	3.2	19
3	A Compact Highly Efficient High-Power Ka-band SiGe HBT Cascode Frequency Doubler With Four-Way Input Transformer Balun. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 2879-2887.	4.6	19
4	A Highly Efficient X-Band Inverse Class-F SiGe HBT Cascode Power Amplifier With Harmonic-Tuned Wilkinson Power Combiner. IEEE Transactions on Circuits and Systems II: Express Briefs, 2018, 65, 1609-1613.	3.0	16
5	An X-band inverse class-F SiGe HBT cascode power amplifier With harmonic-tuned output transformer. , 2017, , .		12
6	High-Power GaN-Based Light-Emitting Diodes Using Thermally Stable and Highly Reflective Nano-Scaled Niâ€“Agâ€“Niâ€“Au Mirror. IEEE Photonics Technology Letters, 2011, 23, 1685-1687.	2.5	11
7	On the Application of Inverse-Mode SiGe HBTs in RF Receivers for the Mitigation of Single-Event Transients. IEEE Transactions on Nuclear Science, 2017, 64, 1142-1150.	2.0	9
8	V-Band Beam-Steering ASK Transmitter and Receiver Using BCB-Based System-on-Package Technology on Silicon Mother Board. IEEE Microwave and Wireless Components Letters, 2011, 21, 619-621.	3.2	8
9	A Compact, Active SiGe Power Divider With Multi-Octave Bandwidth. IEEE Microwave and Wireless Components Letters, 2016, 26, 945-947.	3.2	6
10	A New Emitter-Base-Collector-Base-Emitter SiGe HBT for High Power, Single-Pole Double-Throw X-Band Switches. IEEE Electron Device Letters, 2021, 42, 465-468.	3.9	4
11	A 2â€“24 GHz SiGe HBT Cascode Non-uniform Distributed Power Amplifier Using A Compact, Wideband Two-Section Lumped Element Output Impedance Transformer. , 2021, , .		4
12	An Efficient, Broadband SiGe HBT Non-Uniform Distributed Power Amplifier Leveraging a Compact, Two-Section <i>Î»/4</i> Output Impedance Transformer. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 3524-3533.	4.6	4
13	Co-design of a SiGe BiCMOS X-band, asymmetric, low insertion loss, high power handling SPDT Switch and an Ultra Low Noise LNA for next-generation T/R modules. , 2016, , .		3
14	Advantages of utilizing throughâ€“siliconâ€“vias in <sc>SiGe</sc> HBT RF lowâ€“noise amplifier design. Microwave and Optical Technology Letters, 2015, 57, 2703-2706.	1.4	1
15	Inverse classâ€“<sc>F</sc><sc>X</sc>â€“band <sc>S</sc>i<sc>G</sc>e <sc>HBT</sc> power amplifier with 44% <sc>PAE</sc> and 24.5 d<sc>B</sc>m peak output power. Microwave and Optical Technology Letters, 2016, 58, 2868-2871.	1.4	1
16	A Compact, Low Loss, and Broadband Two-Section Lumped-Element Wilkinson Power Combiner Using 130 nm SiGe HBT BiCMOS Technology. , 2022, , .		0